



#4/Election  
OKing  
5/20/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Bojarczuk, Jr., et al.

Serial No.: 09/755,164

Group Art Unit: 2823

Filed: January 8, 2001

Examiner: Berezny, Neal

For: ALUMINUM NITRIDE AND ALUMINUM OXIDE/ALUMINUM NITRIDE  
HETEROSTRUCTURE GATE DIELECTRIC STACK BASED FIELD  
EFFECT TRANSISTORS AND METHOD FOR FORMING SAME

Honorable Assistant Commissioner of Patents

Washington, D.C. 20231

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MAY 28 2002  
TC 2800 MAIL ROOM

RESPONSE TO FIRST OFFICE ACTION AND  
RESTRICTION REQUIREMENT

Sir:

In response to the Office Action dated May 6, 2002, please consider the following:

REMARKS

In response to the Examiner's restriction requirement, Applicant hereby elects the invention of Group I (e.g., drawn to an Al Nitride gate stack FET as defined by claims 1-18, 21, 23, 25, and 27), without traverse. Applicant reserves the opportunity to file a Divisional Application for the non-elected invention later.

Early, favorable prosecution on the merits is respectfully requested.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.